

Notice of References Cited	Application/Control No. 10/748,821	Applicant(s)/Patent Under Reexamination OHTO ET AL.	
	Examiner Jarrett J. Stark	Art Unit 2823	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0235710	12-2003	Grill et al.	428/641
	B	US-			
	C	US-			
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

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	W	Mark A. Petrich, Karen K. Gleason, and Jeffrey A. Reimer; Structure and properties of amorphous hydrogenated silicon carbide, Phys. Rev. B 36, 9722–9731 (1987)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.